

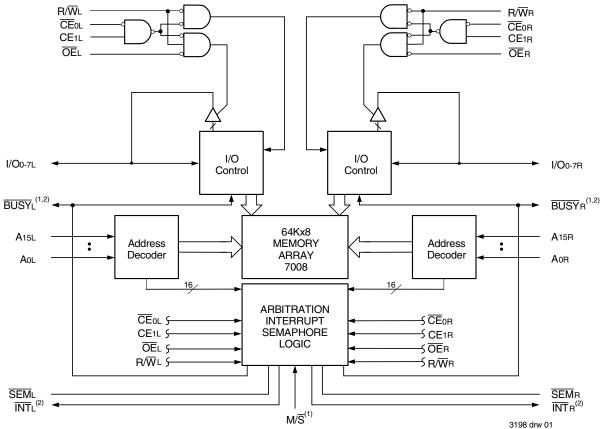
HIGH-SPEED 64K x 8 DUAL-PORT STATIC RAM

Features

- True Dual-Ported memory cells which allow simultaneous reads of the same memory location
- High-speed access
 - Commercial: 15/25/35/55ns (max.)
 - Industrial: 20ns (max.)
- Low-power operation
 - IDT7008S
 Active: 750mW (typ.)
 - Standby: 5mW (typ.) – IDT7008L Active: 750mW (typ.)
 - Standby: 1mW (typ.)
- Dual chip enables allow for depth expansion without external logic

- IDT7008 easily expands data bus width to 16 bits or more using the Master/Slave select when cascading more than one device
- M/S = VIH for BUSY output flag on Master, M/S = VIL for BUSY input on Slave
- Interrupt Flag
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- * Fully asynchronous operation from either port
- TTL-compatible, single 5V (±10%) power supply
- Available in 84-pin PGA, 84-pin PLCC, and a 100-pin TQFP
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information





NOTES:

1. $\overline{\text{BUSY}}$ is an input as a Slave (M/S = VIL) and an output when it is a Master (M/S = VIH).

2. BUSY and INT are non-tri-state totem-pole outputs (push-pull).



7008S/L High-Speed 64K x 8 Dual-Port Static RAM

Description

The IDT7008 is a high-speed 64K x 8 Dual-Port Static RAM. The IDT7008 is designed to be used as a stand-alone 512K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 16-bit-or-more word systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 16-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

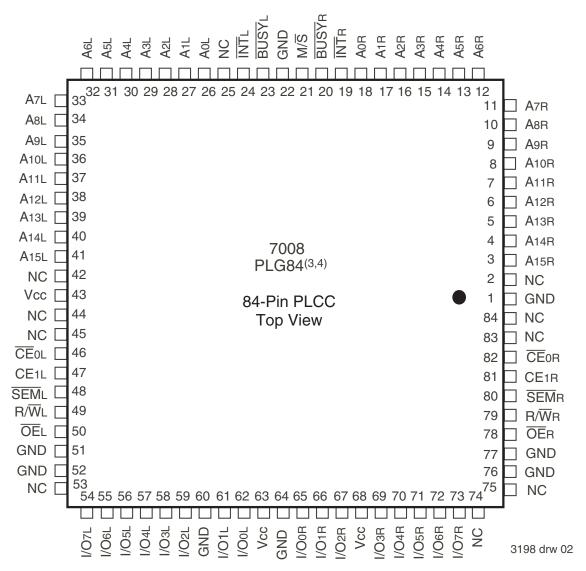
This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for

reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (\overline{CE}_0 and CE1) permit the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using a CMOS high-performance technology, these devices typically operate on only 750mW of power.

The IDT7008 is packaged in a 84-pin Ceramic Pin Grid Array (PGA), a 84-pin Plastic Leadless Chip Carrier (PLCC) and a 100-pin Thin Quad Flatpack (TQFP).

Pin Configurations^(1,2)



NOTES:

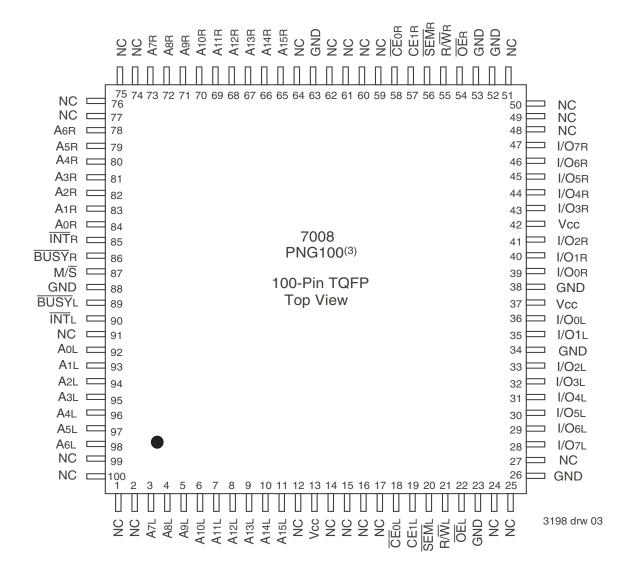
1. All Vcc pins must be connected to power supply.

2. Package body is approximately 1.15 in x 1.15 in x .17 in.

3. This package code is used to reference the package diagram.

4. All GND pins must be connected to ground supply.

Pin Configurations^(1,2) (con't.)



NOTES:

- 1. All Vcc pins must be connected to power supply.
- 2. Package body is approximately 14mm x 14mm x 1.4mm.
- 3. This package code is used to reference the package diagram.

Pin Configurations^(1,2) (con't)

	63	61	60	58	55	54	51	48	46	45	42
11	A7R	A9R	A10R	A12R	A15R	NC	NC	SEMR	ŌĒR	GND	NC
	66	64	62	59	56	49	50	47	44	43	40
10	A4R	A6R	A8R	A11R	A14R	CE1R	CE 0R	R/WR	GND	NC	I/O6R
	67	65			57	53	52		1	41	39
09	A3R	A5R			A13R	GND	NC			I/O7R	I/O5R
	69	68						1		38	37
08	A1R	A2R					I/O4R	I/O3R			
	72	71	73						33	35	34
07	BUSYR	ĪNTR	M∕S			7008			I/O0R	I/O2R	I/O1R
	75	70	74		(GU84 ^{(3,4}	+)		32	31	36
06	BUSYL	A0R	GND			I-PIN PC			GND	Vcc	Vcc
	76	77	78		TC	OP VIEW	/(5)		28	29	30
05	INTL	NC	Aol						GND	I/O1∟	I/Ool
	79	80								26	27
04	A1L	A2L								I/O3L	I/O2L
	81	83			7	11	12			23	25
03	АзL	A5L			A13L	Vcc	NC			I/O6L	I/O4L
	82	1	2	5	8	10	14	17	20	22	24
02	A4L	A7L	A8L	A11L	A14L	NC	CEOL	R/WL	GND	I/O7L	I/O5L
	84	3	4	6	9	15	13	16	18	19	21
01	A6L	A9L	A10L	A12L	A15L	ŌĒL	GND	NC			
1	A	В	С	D E F G H J							L
/										31	98 drw 04
INDEX											

NOTES:

- 1. All Vcc pins must be connected to power supply.
- All GND pins must be connected to ground supply.
 Package body is approximately 1.12 in x 1.12 in x .16 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part marking.

Pin Names

Left Port	Right Port	Names		
CEOL, CE1L	\overline{CE} OR, CE1R	Chip Enables		
R/WL	R/Wr	Read/Write Enable		
ŌĒL	OER Output Enable			
Aol - A15l	Aor - A15r	Address		
1/Ool - 1/O7l	I/O0r - I/O7r	Data Input/Output		
SEML	SEM R	Semaphore Enable		
ĪNTL	Ī NT R	Interrupt Flag		
BUSYL	BUSY R	Busy Flag		
N	I∕S	Master or Slave Select		
V	СС	Power		
G	ND	Ground		



Truth	n Table I:	Chip Er	าอ	able ⁽¹⁾

ĒĒ	Ē	CE1	Mode
	Vil	Vін	Port Selected (TTL Active)
L	<u><</u> 0.2V	<u>></u> Vcc -0.2V	Port Selected (CMOS Active)
	Vih	Х	Port Deselected (TTL Inactive)
	X VIL		Port Deselected (TTL Inactive)
Н	<u>></u> Vcc -0.2V	Х	Port Deselected (CMOS Inactive)
	Х	<u><</u> 0.2V	Port Deselected (CMOS Inactive)

NOTES:

1. Chip Enable references are shown above with the actual \overline{CE}_0 and CE1 levels, \overline{CE} is a reference only.

Truth Table II: Non-Contention Read/Write Control

	Inputs ⁽¹⁾			Outputs	
CE ⁽²⁾	R/W	ŌĒ	SEM	I/O0-7	Mode
Н	Х	Х	Н	High-Z	Deselected: Power-Down
L	L	Х	Н	DATAIN	Write to memory
L	Н	L	Н	DATAOUT	Read memory
Х	Х	Н	Х	High-Z	Outputs Disabled
NOTES	NOTEC				3198 tbl 03

NOTES:

1. Aol – A15L \neq Aor – A15R.

2. Refer to Chip Enable Truth Table.

Truth Table III: Semaphore Read/Write Control⁽¹⁾

	Inp	uts		Outputs	
CE ⁽²⁾	R/₩	ŌĒ	SEM	I/O0-7	Mode
Н	Н	L	L	DATAOUT	Read Semaphore Flag Data Out
Н	\uparrow	Х	L	DATAIN	Write I/Oo into Semaphore Flag
L	Х	Х	L	_	Not Allowed

NOTES:

1. There are eight semaphore flags written to via I/Oo and read from all the I/Os (I/Oo-I/O7). These eight semaphore flags are addressed by Ao-A2.

2. Refer to Chip Enable Truth Table.



Industrial and Commercial Temperature Ranges

3198 tbl 02

7008S/L High-Speed 64K x 8 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
lout	DC Output Current	50	mA
			3198 tbl 05

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

$Maximum \ Operating \ Temperature \ and \ Supply \ Voltage^{(1)}$

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

3198 tbl 06

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
Vih	Input High Voltage	2.2		6.0 ⁽²⁾	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾		0.8	V

NOTES:

1. VIL \geq -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

Capacitance

$(TA = +25^{\circ}C, f = 1.0mhz)$ (TQFP Only)

Symbol	Parameter	Conditions	Мах.	Unit			
Cin	Input Capacitance	VIN = 0V	9	pF			
Cout ⁽²⁾	Output Capacitance	Vout = 0V	10	pF			
3198 tbl 08							

NOTES:

- 1. This parameter is determined by device characterization but is not production tested.
- 2. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽²⁾ ($Vcc = 5.0V \pm 10\%$)

			7008S		7008L		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
LL	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, VIN = 0V to Vcc	_	10	_	5	μA
Ilo	Output Leakage Current	\overline{CE} = VIH, VOUT = 0V to VCC	_	10	_	5	μA
Vol	Output Low Voltage	Iol = 4mA	_	0.4	_	0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4		2.4		V

NOTES:

1. At Vcc ≤ 2.0V, input leakages are undefined.

2. Refer to Chip Enable Truth Table.



3198 tbl 07

3198 tbl 09

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,6) ($Vcc = 5.0V \pm 10\%$)

				Version T		3X15 I Only		3X20 & Ind		3X25 Only	
Symbol	Parameter	Test Condition	Versio			Max.	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	\overline{CE} = VIL, Outputs Disabled SEM = VIH f = fmax ⁽³⁾	COM'L	S L	205 200	365 325	190 180	325 285	180 170	305 265	mA
(1		T = TMAX ⁽⁴⁾	IND	S L			 180	 335			
ISB1	Standby Current (Both Ports - TTL Level		COM'L	S L	65 65	110 90	50 50	90 70	40 40	85 60	mA
	Inputs)		IND	S L			 50	 85			
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^{*}A^{*} = VIL \text{ and } \overline{CE}^{*}B^{*} = VIH^{(5)}$ Active Port Outputs Disabled, f=fMAX ⁽³⁾	COM'L	S L	130 130	245 215	115 115	215 185	105 105	200 170	mA
	inputs)	$\frac{1 = IMAX^{(5)}}{SEMR} = \frac{SEM}{SEM}L = VIH$	IND	S L			 115	 220			
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports $\overline{CE}L$ and $\overline{CER} \ge VCC - 0.2V$	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	mA
		$ \begin{array}{l} \text{VIN} \geq V\text{CC} - 0.2\text{V or} \\ \frac{\text{VIN} \leq 0.2\text{V, } f = 0^{(4)}}{\text{SEMR} = \text{SEML} \geq \text{VCC} - 0.2\text{V} } \end{array} $	IND	S L			 0.2	 10			
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\overline{CE}^{"A"} \le 0.2V$ and $\overline{CE}^{"B"} \ge Vcc - 0.2V^{(5)}$	COM'L	S L	120 120	220 190	110 110	190 160	100 100	170 145	mA
		$\label{eq:semiclosed} \begin{array}{l} \overline{\text{SEMR}} = \overline{\text{SEML}} \geq \text{VCC} & -0.2\text{V} \\ \overline{\text{VIN}} \geq \text{VCC} & -0.2\text{V} \text{ or } \overline{\text{VIN}} \leq 0.2\text{V} \\ \text{Active Port Outputs Disabled} \\ f = fMax^{(3)} \end{array}$	IND	S L			 110	— 195			

						3X35 I Only		8X55 & Ind	
Symbol	Parameter	Test Condition	Versio	n	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Мах.	Un
ICC	Dynamic Operating Current (Both Ports Active)	$\overline{CE} = VIL, Outputs DisabledSEM = VIH$	COM'L	S L	160 160	295 255	150 150	270 230	m
		$f = fMAX^{(3)}$	IND	S L			150 150	310 270	
ISB1	Standby Current (Both Ports - TTL Level	$\label{eq:cell} \begin{split} \overline{CE}_L &= \overline{CE}_R = VIH\\ \overline{SEMR} &= \overline{SEML} = VIH \end{split}$	COM'L	S L	30 30	85 60	20 20	85 60	n
	Inputs)		IND	S L			13 13	100 80	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^{*}A^{*} = VIL \text{ and } \overline{CE}^{*}B^{*} = VIH^{(5)}$ Active Port Outputs Disabled, f=fMax ⁽³⁾	COM'L	S L	95 95	185 155	85 85	165 135	r
	inputs)	$\overline{\text{SEMR}} = \overline{\text{SEML}} = \text{Vih}$	IND	S L			85 85	195 165	
ISB3	Full Standby Current (Both Ports - All CMOS	Both Ports $\overline{CE}L$ and $\overline{CER} \ge VCC - 0.2V$	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	r
	Level Inputs)	$ \begin{array}{l} \mbox{ViN} \geq \mbox{Vcc} - 0.2 \mbox{V or} \\ \mbox{ViN} \leq 0.2 \mbox{V}, f = 0^{(4)} \\ \mbox{SEMR} = \mbox{SEML} \geq \mbox{Vcc} - 0.2 \mbox{V} \end{array} $	IND	S L			1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\frac{\overline{CE}^*A^*}{\overline{CE}^*B^*} \leq 0.2V \text{ and}$ $\frac{\overline{CE}^*B^*}{\overline{CE}^*B^*} \geq V_{CC} - 0.2V^{(5)}$	COM'L	S L	90 90	160 135	80 80	135 110	r
		SEMR = SEML \geq VCC - 0.2V VIN \geq VCC - 0.2V or VIN \leq 0.2V Active Port Outputs Disabled f = fMAX ⁽³⁾	IND	S L			80 80	175 150]

NOTES:

1. 'X' in part numbers indicates power rating (S or L)

2. Vcc = 5V, TA = +25°C, and are not production tested. Icccc = 120mA (Typ.)

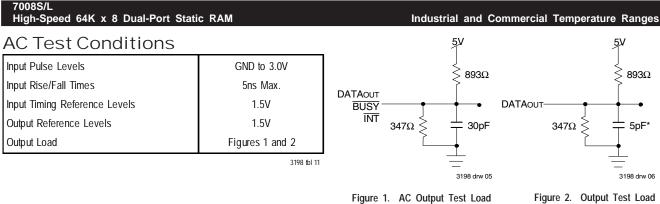
3. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/ trc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

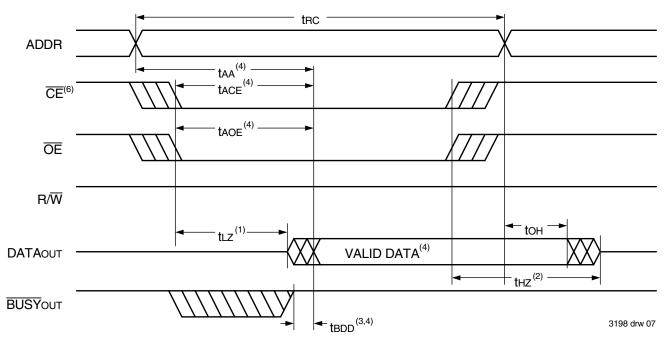
6. Refer to Chip Enable Truth Table.



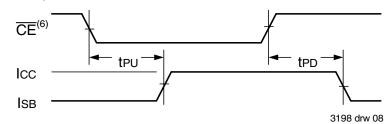


(for tLz, tHz, twz, tow) * Including scope and jig.

Waveform of Read Cycles⁽⁵⁾



Timing of Power-Up Power-Down



NOTES:

- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}.$
- 2. Timing depends on which signal is de-asserted first $\overline{\text{CE}}$ or $\overline{\text{OE}}.$
- 3. tbbb delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last take, take, take or tBDD.
- 5. $\overline{\text{SEM}} = \text{VIH}.$
- 6. Refer to Chip Enable Truth Table.



Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

			BX15 I Only		3X20 & Ind		8X25 'I Only		8X35 'I Only		8X55 & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CY	CLE	-		-		-	-		-			
trc	Read Cycle Time	15		20		25		35		55		ns
taa	Address Access Time		15		20		25		35		55	ns
tace	Chip Enable Access Time ⁽⁴⁾		15		20		25		35		55	ns
taoe	Output Enable Access Time		10		12		13		20		30	ns
toн	Output Hold from Address Change	3		3		3		3		3		ns
tlz	Output Low-Z Time ^(1,2)	3		3		3		3		3		ns
tHZ	Output High-Z Time ^(1,2)		10		12		15		15		25	ns
tpu	Chip Enable to Power Up Time ⁽²⁾	0		0		0		0		0		ns
tpd	Chip Disable to Power Down Time ⁽²⁾		15		20		25		35		50	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	10		10		12		15		15		ns
tsaa	Semaphore Address Access Time		15		20		25		35		55	ns

3198 tbl 12

3198 tbl 13

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁶⁾

		7008X15 Com'l Only			7008X20 Com'l & Ind		7008X25 Com'l Only		3X35 I Only	7008X55 Com'l & Ind		
Symbol	Parameter	Min.	Мах.	Min.	Max.	Min.	Мах.	Min.	Мах.	Min.	Max.	Unit
WRITE C	WRITE CYCLE											
twc	Write Cycle Time	15		20		25		35		55		ns
tew	Chip Enable to End-of-Write ⁽³⁾	12		15		20		30		45		ns
taw	Address Valid to End-of-Write	12		15		20		30		45		ns
tas	Address Set-up Time ⁽³⁾	0		0		0		0		0		ns
twp	Write Pulse Width	12		15		20		25		40		ns
twr	Write Recovery Time	0		0	_	0		0		0		ns
tow	Data Valid to End-of-Write	10		15		15		15		30		ns
tнz	Output High-Z Time ^(1,2)		10		12		15		15		25	ns
tdн	Data Hold Time ⁽⁵⁾	0		0		0		0		0		ns
twz	Write Enable to Output in High-Z ^(1,2)		10		12		15		15		25	ns
tow	Output Active from End-of-Write ^(1,2,5)	0		0		0		0		0		ns
tswrd	SEM Flag Write to Read Time	5		5		5		5		5		ns
tsps	SEM Flag Contention Window	5		5		5		5		5		ns

NOTES:

1. Transition is measured 0mV from Low- or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested.

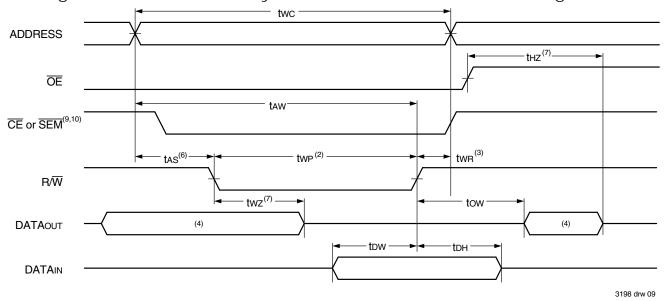
3. To access RAM, $\overline{CE} = V_{IL}$ and $\overline{SEM} = V_{IH}$. To access semaphore, $\overline{CE} = V_{IH}$ and $\overline{SEM} = V_{IL}$. Either condition must be valid for the entire tew time. 4. To access RAM, $\overline{CE} = V_{IL}$ and $\overline{SEM} = V_{IH}$. To access semaphore, $\overline{CE} = V_{IH}$ and $\overline{SEM} = V_{IL}$.

5. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

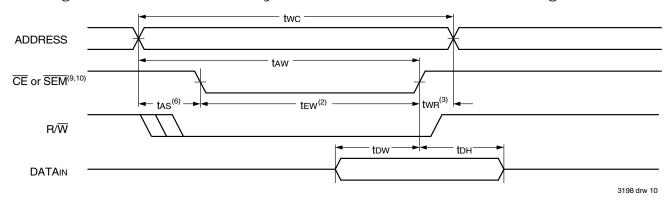
6. 'X' in part numbers indicates power rating (s or L).

Industrial and Commercial Temperature Ranges

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing^(1,5,8)



Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,5)

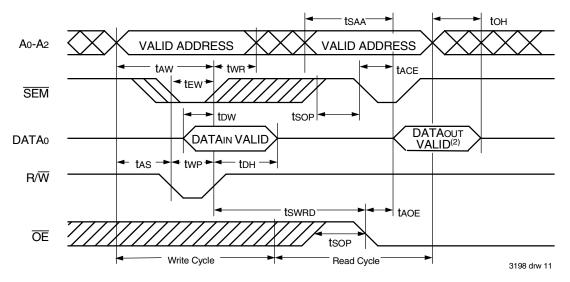


NOTES:

- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a LOW CE and a LOW R/W for memory array writing cycle.
- 3. twr is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, \overline{CE} or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is LOW during R \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If \overline{OE} is HIGH during an R/ \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. tew must be met for either condition.

10. Refer to Chip Enable Truth Table.

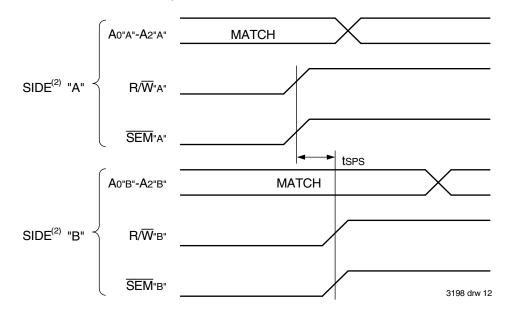
Timing Waveform of Semaphore Read after Write Timing, Either Side⁽¹⁾



NOTES:

- 1. $\overline{CE} = V_{IH}$ for the duration of the above timing (both write and read cycle) (Refer to Chip Enable Truth Table).
- 2. "DATAOUT VALID" represents all I/O's (I/Oo I/O15) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



NOTES:

- 1. DOR = DOL = VIL, $\overline{CE}L = \overline{CE}R = VIH$ (Refer to Chip Enable Truth Table).
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. "B" is the opposite from port "A".
- 3. This parameter is measured from R/W*A* or SEM*A* going HIGH to R/W*B* or SEM*B* going HIGH.
- 4. If tsps is not satisfied, the semaphore will fall positively to one side or the other, but there is no guarantee which side will obtain the flag.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

			7008X15 Com'l Only		7008X20 Com'l & Ind		3X25 I Only		8X35 I Only	7008X55 Com'l & Ind		
Symbol	Parameter	Min.	Мах.	Min.	Max.	Min.	Мах.	Min.	Мах.	Min.	Мах.	Unit
BUSY TIN	IING (M/S=Viн)	-	-									
tbaa	BUSY Access Time from Address Match		15		20		20		20	_	45	ns
tbda	BUSY Disable Time from Address Not Matched		15		20		20		20		40	ns
t BAC	BUSY Access Time from Chip Enable Low		15		20		20		20		40	ns
tbdc	BUSY Access Time from Chip Enable High		15		17		17		20		35	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		5		5		5		ns
tbdd	BUSY Disable to Valid Data ⁽³⁾		15		20		25		35	_	55	ns
twн	Write Hold After BUSY ⁽⁵⁾	12		15		17		25		25		ns
BUSY TIN	IING (M/ S =VIL)											
twв	BUSY Input to Write ⁽⁴⁾	0		0		0		0		0		ns
twн	Write Hold After BUSY ⁽⁵⁾	12		15		17		25		25		ns
PORT-TO-	PORT DELAY TIMING											
twdd	Write Pulse to Data Delay ⁽¹⁾		30		45		50		60		80	ns
tddd	Write Data Valid to Read Data Delay ⁽¹⁾		25		30		35		45		65	ns

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VIH)".

2. To ensure that the earlier of the two ports wins.

3. tBDD is a calculated parameter and is the greater of 0, tWDD - tWP (actual) or tDDD - tDW (actual).

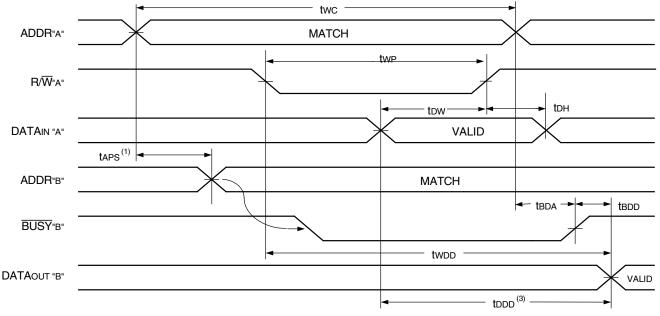
4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".

5. To ensure that a write cycle is completed on port "B" after contention on port "A".

6. 'X' in part numbers indicates power rating (S or L).

3198 drw 13

Timing Waveform of Write with Port-to-Port Read and $\overline{\text{BUSY}}^{(2,5)}$ (M/ $\overline{\text{S}}$ = VIH)⁽⁴⁾

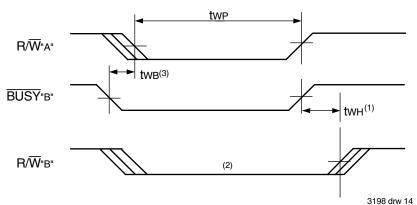


NOTES:

- 1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = V_{IL}$ (SLAVE).
- 2. $\overline{CE}_{L} = \overline{CE}_{R} = V_{IL}$, refer to Chip Enable Truth Table.
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. If $M/\overline{S} = V_{IL}$ (SLAVE), then \overline{BUSY} is an input ($\overline{BUSY}^*A^* = V_{IH}$ and $\overline{BUSY}^*B^* =$ "don't care", for this example).

5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

Timing Waveform of Write with **BUSY** (M/S = VIL)

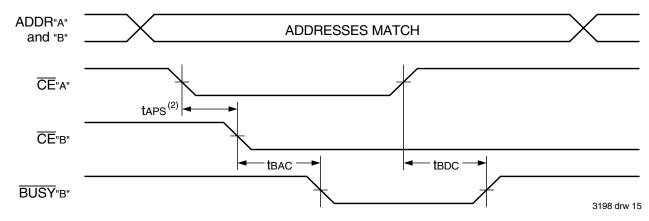


NOTES:

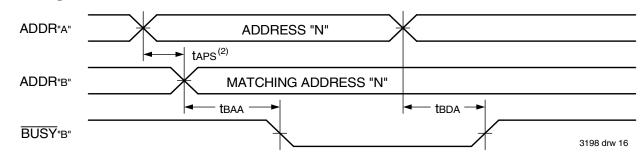
- 1. twh must be met for both $\overline{\text{BUSY}}$ input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb is only for the 'Slave' version.

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Waveform of **BUSY** Arbitration Controlled by \overline{CE} Timing^(1,3) (M/ \overline{S} = VIH)



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing⁽¹⁾ (M/S = VIH)



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. If tAPS is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

3. Refer to Chip Enable Truth Table.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

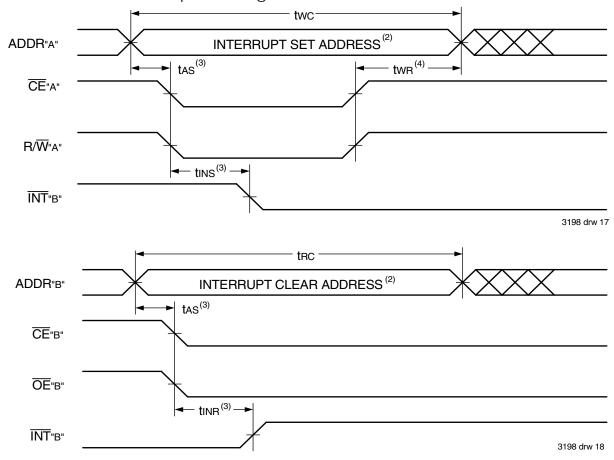
			3X15 Only		3X20 & Ind		8X25 I Only		3X35 I Only		3X55 & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	Unit
INTERRUP	t timing											
tas	Address Set-up Time	0		0		0		0		0		ns
twr	Write Recovery Time	0		0		0		0		0		ns
tins	Interrupt Set Time	I	15		20		20		25		40	ns
tinr	Interrupt Reset Time		15		20		20		25		40	ns

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

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Waveform of Interrupt Timing^(1,5)



NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. See Interrupt Truth Table.
- 3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
- 4. Timing depends on which enable signal $(\overline{CE} \text{ or } R/\overline{W})$ is de-asserted first.
- 5. Refer to Chip Enable Truth Table.

Left Port					Right Port					
R/₩L	ĈĒ		A15L-A0L	ĪNTL	R/WR	ĈĒ		A15R-A0R	ĪNTR	Function
L	L	Х	FFFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	FFFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	FFFE	Х	Set Left INTL Flag
Х	L	L	FFFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

Truth Table IV — Interrupt Flag^(1,4,5)

NOTES:

1. Assumes $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = V_{IH}$.

2. If $\overline{\text{BUSY}}L = VIL$, then no change.

3. If $\overline{\text{BUSY}}_{R} = \text{VIL}$, then no change.

4. $\overline{\text{INT}}_{\text{L}}$ and $\overline{\text{INT}}_{\text{R}}$ must be initialized at power-up.

5. Refer to Chip Enable Truth Table.

3198 tbl 16

Truth Table V — Address **BUSY** Arbitration⁽⁴⁾

	Inputs			puts	
CEL	CER	Aol-A15l Aor-A15r	BUS YL ⁽¹⁾	BUSY _R ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

3198 tbl 17

1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT7008 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.

 "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

4. Refer to Chip Enable Truth Table

Truth Table VI — Example of Semaphore Procurement Sequence^(1,2,3)

Functions	Do - D7 Left	Do - D7 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT7008.

2. There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O7). These eight semaphores are addressed by Ao-A2.

3. $\overline{CE} = V_{IH}$, $\overline{SEM} = V_{IL}$ to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

Functional Description

The IDT7008 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7008 has an automatic power down feature controlled by \overline{CE} . The \overline{CE} and CE_1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected (\overline{CE} HIGH). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag

(INTL) is asserted when the right port writes to memory location FFFE (HEX), where a write is defined as $\overline{CE}_R = R/W_R = V_{IL}$ per the Truth Table. The left port clears the interrupt through access of address location FFFE when $\overline{CE}_L = \overline{OE}_L = V_{IL}$, R/W is a "don't care". Likewise, the right port interruptflag (\overline{INT}_R) is asserted when the left port writes to memory location FFFF (HEX) and to clear the interrupt flag (\overline{INT}_R), the right port must read the memory location FFFF. The message (8 bits) at FFFE or FFFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations FFFE and FFFF are not used as mail boxes, but as part of the random access memory. Refer to Table IV for the interrupt operation.



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Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a $\overline{\text{BUSY}}$ indication, the write signal is gated internally to prevent the write from proceeding.

The use of $\overline{\text{BUSY}}$ logic is not required or desirable for all applications. In some cases it may be useful to logically OR the $\overline{\text{BUSY}}$ outputs together and use any $\overline{\text{BUSY}}$ indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of $\overline{\text{BUSY}}$ logic is not desirable, the $\overline{\text{BUSY}}$ logic can be disabled by placing the part in slave mode with the M/\overline{S} pin. Once in slave mode the $\overline{\text{BUSY}}$ pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the $\overline{\text{BUSY}}$ pins HIGH. If desired, unintended write operations can be prevented to a port by tying the $\overline{\text{BUSY}}$ pin for that port LOW.

The BUSY outputs on the IDT7008 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

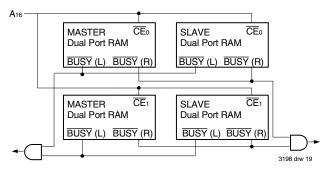


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7008 RAMs.

Width Expansion Busy Logic Master/Slave Arrays

When expanding an IDT7008 RAM array in width while using \overline{BUSY} logic, one master part is used to decide which side of the RAMs array will receive a \overline{BUSY} indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the \overline{BUSY} signal as a write inhibit signal. Thus on the IDT7008 RAM the \overline{BUSY} pin is an output if the part is used as a master (M/ \overline{S} pin = VIH), and the \overline{BUSY} pin is an input if the part used as a slave (M/ \overline{S} pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with the R/W signal. Failure to observe this timing can

result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT7008 is an extremely fast Dual-Port 64K x 8 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by \overrightarrow{CE} , the Dual-Port RAM enable, and SEM, the semaphore enable. The CE and SEM pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table II where \overrightarrow{CE} and \overrightarrow{SEM} are both HIGH.

Systems which can best use the IDT7008 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT7008s hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT7008 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very highspeed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via

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the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

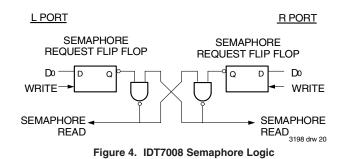
The eight semaphore flags reside within the IDT7008 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a LOW input on the \overline{SEM} pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{CE} , and R/\overline{W}) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a LOW level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Table VI). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (\overline{SEM} or \overline{OE}) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table VI). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip

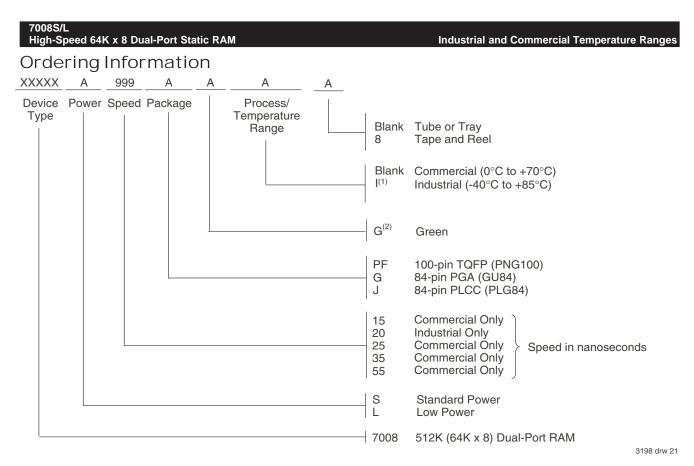


over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.



NOTES:

- 1. Industrial temperature range is available on selected TQFP packages in standard power. For other speeds, packages and powers contact your sales office.
- Green parts available. For specific speeds, packages and powers contact your local sales office. LEAD FINISH (SnPb) parts are Obsolete excluding PGA. Product Discontinuation Notice - PDN# SP-17-02 Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
15	7008L15JG	PLG84	PLCC	С
	7008L15JG8	PLG84	PLCC	С
	7008L15PFG	PNG100	TQFP	С
	7008L15PFG8	PNG100	TQFP	С
20	7008L20JGI	PLG84	PLCC	I
	7008L20JGI8	PLG84	PLCC	I
	7008L20PFGI	PNG100	TQFP	I
	7008L20PFGI8	PNG100	TQFP	I
25	7008L25G	GU84	PGA	С
35	7008L35G	GU84	PGA	С
55	7008L55G	GU84	PGA	С

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
25	7008S25G	GU84	PGA	С
35	7008S35G	GU84	PGA	С
55	7008S55G	GU84	PGA	С

Datasheet Document History

01/06/99:		Initiated datasheet document history
		Converted to new format
		Cosmetic and typographical corrections
	Pages 2 and 3	Added additional notes to pin configurations
06/03/99:	0	Changed drawing format
11/10/99:		Replaced IDT logo
05/08/99:	Page 6	Increased storage temperature parameter
	5	Clarified TA parameter
	Page 7	DC Electrical parameters-changed wording from "open" to "disabled"
	5	Changed ±200mV to 0mV in notes
07/26/04:	Page 2 - 4	Added date revision for pin configurations
	Page 6	Updated Capacitance table
	Page 7	Added 15ns commercial speed grade to the DC Electrical Characteristics
	5	Added 20ns Industrial temp for low power to DC Electrical Characteristics
	Page 9, 12 & 14	Added 15ns commercial speed grade to AC Electrical Characteristics
	5	Added 20ns Industrial temp for low power to AC Electrical Chars for Read, Write, Busy & Interrupt
	Page 19	Added Commercial for 15ns and Industrial temp to 20ns in ordering information
	Page 1 & 19	Replaced old ти logo with new ти logo
04/03/06:	Page 1	Added green availability to features
	Page 19	Added green indicator to ordering information
10/21/08:	Page 19	Removed "IDT" from orderable part number
10/02/14:	Page 19	Added Tape & Reel to Ordering Information
	Page 2, 3, 4 & 19	The package codes for PN100-1, G108-1 & J84-1 changed to PN100, G108 & J84
04/06/16:	Page 2	Changed diagram for the J84 pin configuration by rotating package pin labels and pin
	Ũ	numbers 90 degrees clockwise to reflect pin1 orientation and added pin 1 dot at pin 1
		Removed J84 chamfer and aligned the top and bottom pin labels in the standard direction
	Page 3	Changed diagram for the PN100 pin configuration by rotating package pin labels and pin
	Ũ	numbers 90 degrees counter clockwise to reflect pin 1 orientation and added pin 1 dot at pin 1
		Added the IDT logo, changed the text to be in alignment with new diagram marking specs, removed
		date from all pin configurations and updated footnote references for the J84 & the PN100
	Page 6	Military grade removed from Absolute Max and Max Operating tables
	Page 7, 9, 12 & 14	Military grade removed from all DC Elec & all AC Elec tables for all speeds
	Page 19	Military grade removed from Ordering Information
03/06/18:	-	Product Discontinuation Notice - PDN# SP-17-02
		Last time buy expires June 15, 2018
08/07/19:	Page 1 & 19	Deleted obsolete Commercial speed grade 20ns and Industrial speed grade 55ns
	Page 2, 3 & 4	Updated package codes J84 to PLG84, PN100 to PNG100 and G84 to GU84
	Page 19	Added Orderable Part Information tables
01/05/22:	Page 1 - 21	Source file updated to reflect previous Corporate Marketing rebranding
	Page 2 - 4	Updated package codes

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